

# FQT13N06

## 60V N-Channel MOSFET

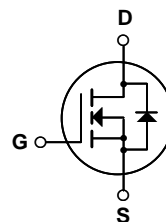
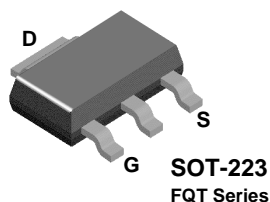
### General Description

These N-Channel enhancement mode power field effect transistors are produced using Fairchild's proprietary, planar stripe, DMOS technology.

This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for low voltage applications such as DC/DC converters, high efficiency switching for power management in portable and battery operated products.

### Features

- 2.8A, 60V,  $R_{DS(on)} = 0.14\Omega @ V_{GS} = 10V$
- Low gate charge ( typical 5.8 nC)
- Low Crss ( typical 15 pF)
- Fast switching
- Improved dv/dt capability



### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	FQT13N06	Units
V <sub>DSS</sub>	Drain-Source Voltage	60	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C) - Continuous (T <sub>C</sub> = 70°C)	2.8	A
		2.24	A
I <sub>DM</sub>	Drain Current - Pulsed (Note 1)	11.2	A
V <sub>GSS</sub>	Gate-Source Voltage	± 25	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy (Note 2)	85	mJ
I <sub>AR</sub>	Avalanche Current (Note 1)	2.8	A
E <sub>AR</sub>	Repetitive Avalanche Energy (Note 1)	0.21	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	7.0	V/ns
P <sub>D</sub>	Power Dissipation (T <sub>C</sub> = 25°C) - Derate above 25°C	2.1	W
		0.017	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C
T <sub>L</sub>	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds	300	°C

### Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient *	--	60	°C/W

\* When mounted on the minimum pad size recommended (PCB Mount)

**Electrical Characteristics**T<sub>C</sub> = 25°C unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	60	--	--	V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250 μA, Referenced to 25°C	--	0.06	--	V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V	--	--	1	μA
		V <sub>DS</sub> = 48 V, T <sub>C</sub> = 150°C	--	--	10	μA
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 25 V, V <sub>DS</sub> = 0 V	--	--	100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -25 V, V <sub>DS</sub> = 0 V	--	--	-100	nA

**On Characteristics**

V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 250 μA	2.0	--	4.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.4 A	--	0.11	0.14	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 25 V, I <sub>D</sub> = 1.4 A (Note 4)	--	3.0	--	S

**Dynamic Characteristics**

C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1.0 MHz	--	240	310	pF
C <sub>oss</sub>	Output Capacitance		--	90	120	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		--	15	20	pF

**Switching Characteristics**

t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 30 V, I <sub>D</sub> = 6.5 A, R <sub>G</sub> = 25 Ω  (Note 4, 5)	--	5	20	ns
t <sub>r</sub>	Turn-On Rise Time		--	25	60	ns
t <sub>d(off)</sub>	Turn-Off Delay Time		--	8	25	ns
t <sub>f</sub>	Turn-Off Fall Time		--	15	40	ns
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = 48 V, I <sub>D</sub> = 13 A, V <sub>GS</sub> = 10 V  (Note 4, 5)	--	5.8	7.5	nC
Q <sub>gs</sub>	Gate-Source Charge		--	2.0	--	nC
Q <sub>gd</sub>	Gate-Drain Charge		--	2.5	--	nC

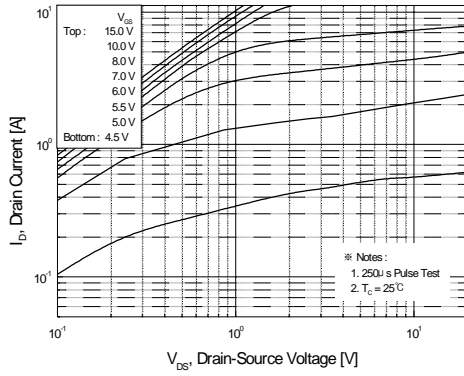
**Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current	--	--	2.8	A	
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current	--	--	11.2	A	
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 2.8 A	--	--	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 13 A,	--	39	--	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs (Note 4)	--	40	--	nC

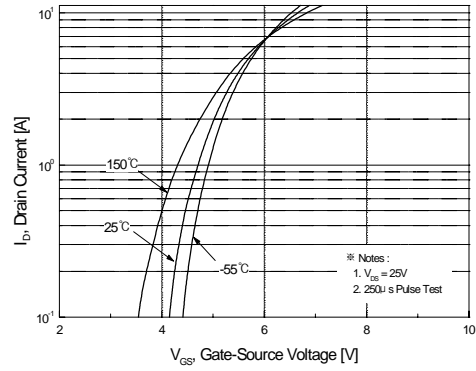
**Notes:**

1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 12.6mH, I<sub>AS</sub> = 2.8A, V<sub>DD</sub> = 25V, R<sub>G</sub> = 25 Ω, Starting T<sub>J</sub> = 25°C
3. I<sub>SD</sub> ≤ 13A, di/dt ≤ 300A/μs, V<sub>DD</sub> ≤ BV<sub>DSS</sub>, Starting T<sub>J</sub> = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

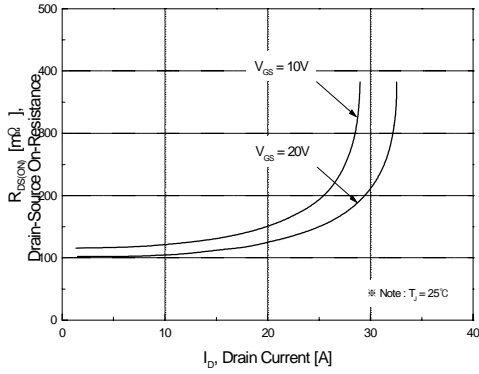
## Typical Characteristics



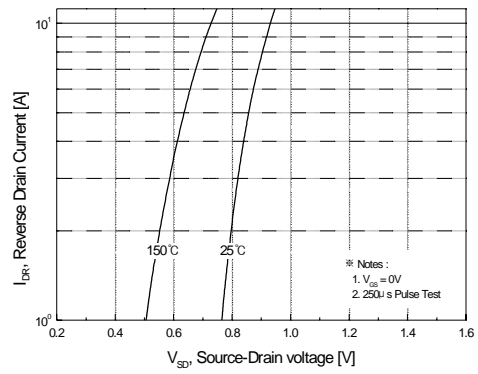
**Figure 1. On-Region Characteristics**



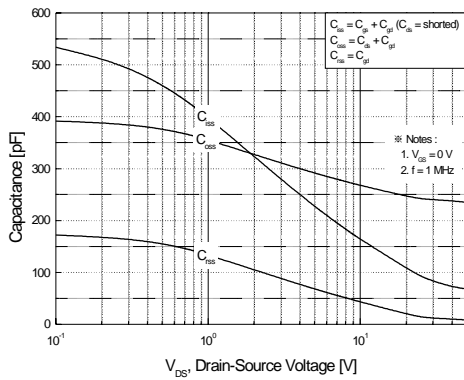
**Figure 2. Transfer Characteristics**



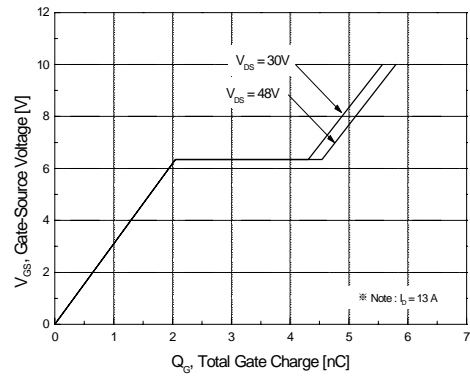
**Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature**

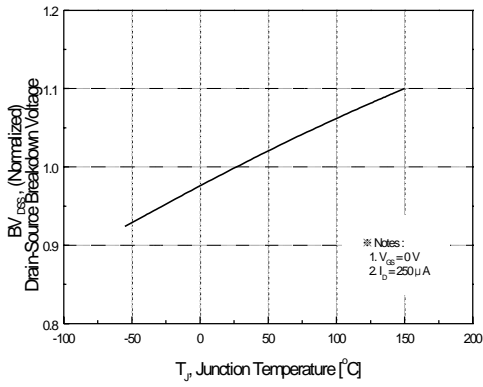


**Figure 5. Capacitance Characteristics**

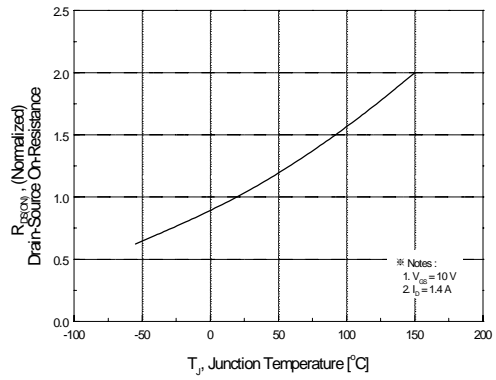


**Figure 6. Gate Charge Characteristics**

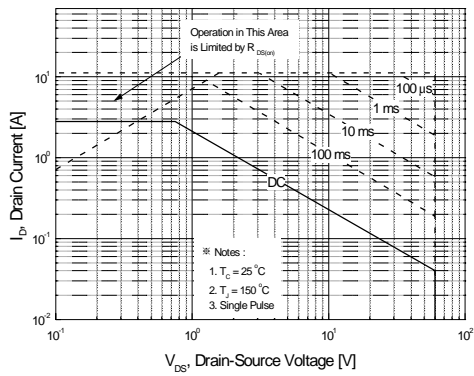
**Typical Characteristics** (Continued)



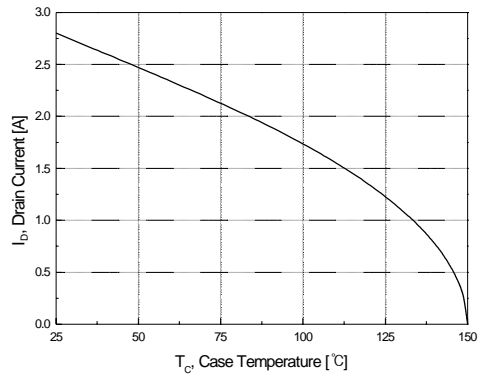
**Figure 7. Breakdown Voltage Variation vs. Temperature**



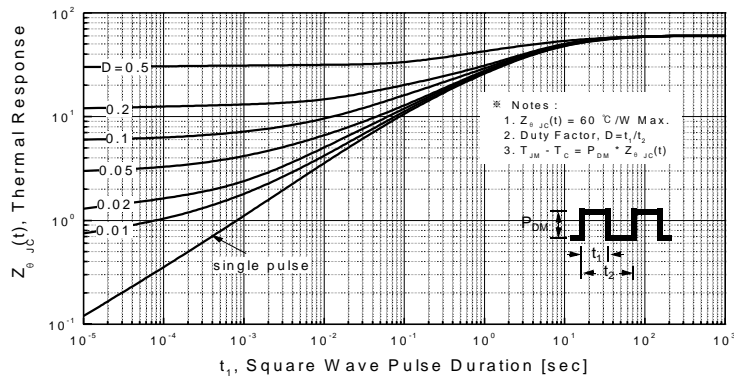
**Figure 8. On-Resistance Variation vs. Temperature**



**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Drain Current vs. Case Temperature**

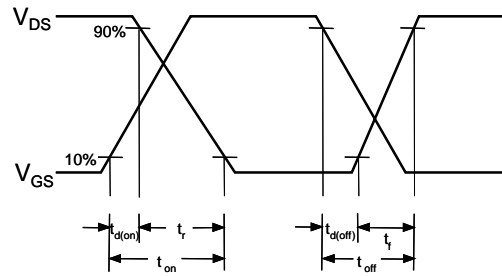


**Figure 11. Transient Thermal Response Curve**

**Gate Charge Test Circuit & Waveform**



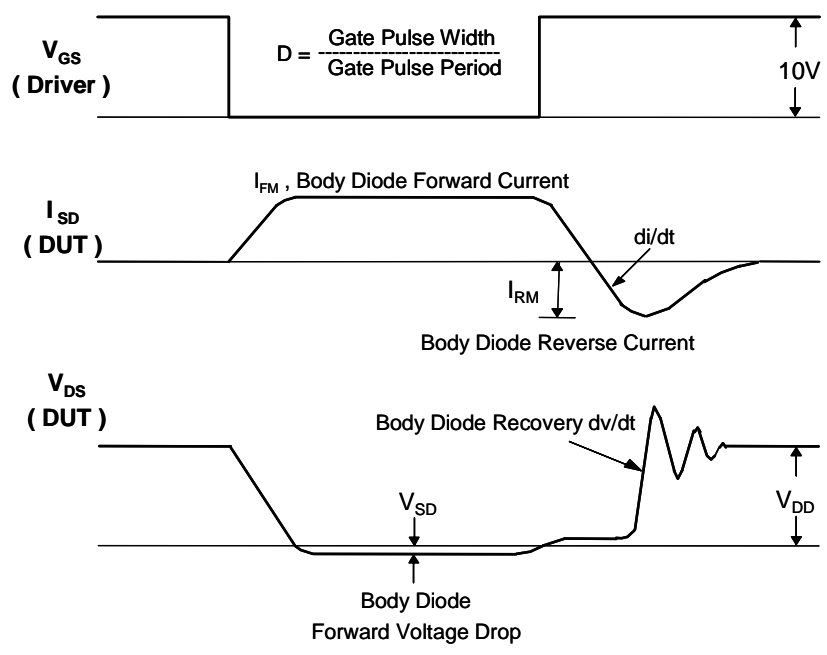
**Resistive Switching Test Circuit & Waveforms**



**Unclamped Inductive Switching Test Circuit & Waveform**



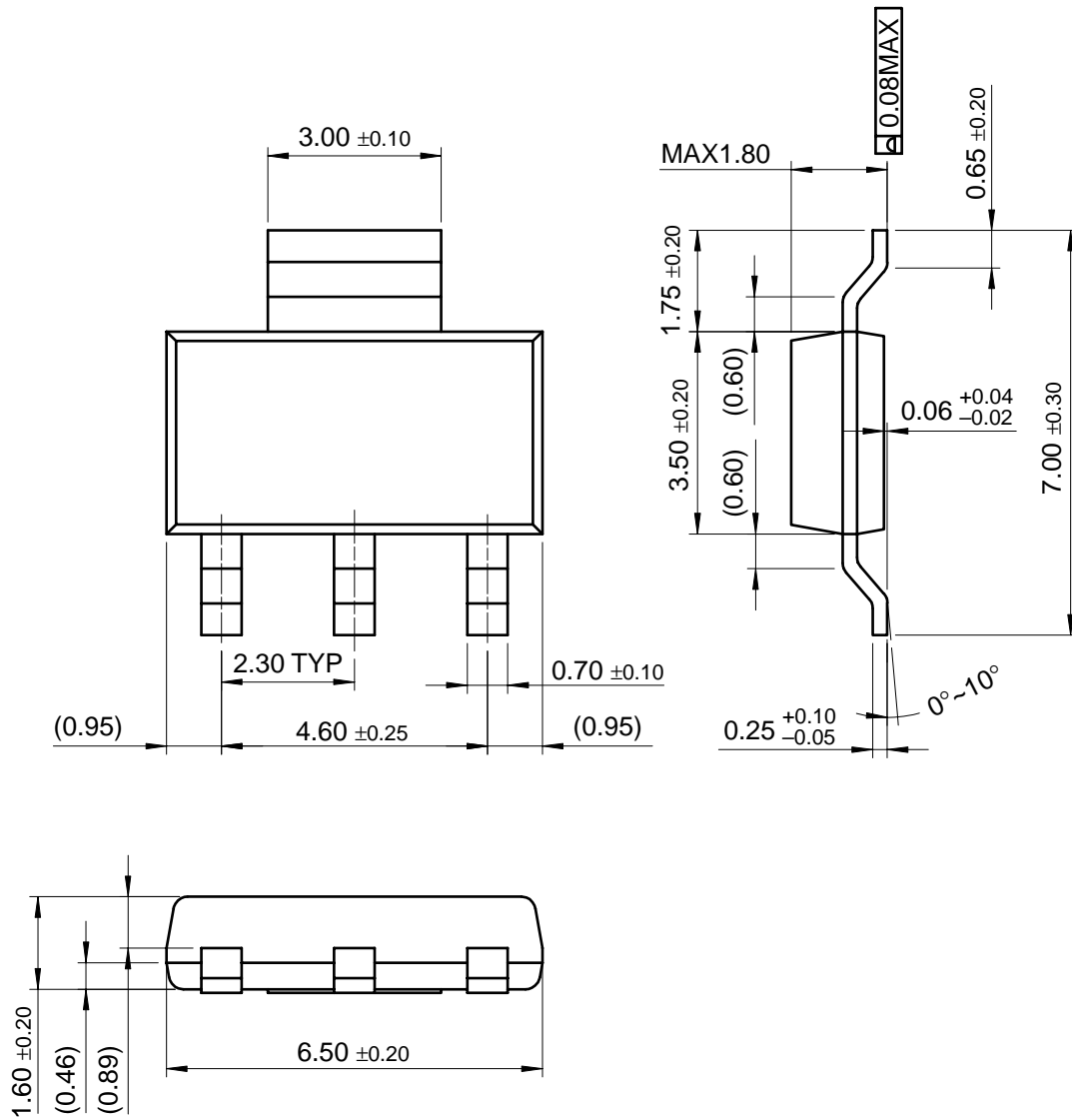
Peak Diode Recovery dv/dt Test Circuit & Waveforms



Package Dimensions

FQT13N06

SOT-223



Dimensions in Millimeters

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